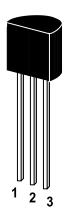
NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into three groups, D, E and F, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25℃)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	15	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	700	mA
Collector Peak Current	ic(peak)	1000	mA
Power Dissipation	P _{tot}	500	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







ST 2SD655

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at $V_{CE}=1V$, $I_{C}=150mA$					
Current Gain Group D	h _{FE}	250	-	500	-
E	h _{FE}	400	-	800	-
F	h _{FE}	600	-	1200	-
Collector to Base Breakdown Voltage					
at I _C =10μA	$V_{(BR)CBO}$	30	-	-	V
Collector to Emitter Breakdown Voltage					
at I _C =1mA	$V_{(BR)CEO}$	15	-	-	V
Emitter Base Breakdown Voltage					
at I _E =10μA	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
at V _{CB} =20V	I _{CBO}	-	-	1	μΑ
Base Emitter Voltage					
at $V_{CE}=1V$, $I_{C}=150mA$	V_{BE}	-	-	1	V
Collector Emitter Saturation Voltage					
at $I_C=500$ mA, $I_B=50$ mA	$V_{CE(sat)}$	-	0.15	0.5	V
Gain Bandwidth Product					
at V _{CE} =1V, I _C =150mA	f _T		250		MHz









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